Supporting Information

Oxygen vacancy-dependent photocatalytic activity of well-defined $Bi_2Sn_2O_{7-x}$ hollow nanocubes for NO_x removal

Yanfeng Lu^{a,b}, Meijuan Chen^c, Tingting Huang^a, Yu Huang^{a,b,*}, Jun-ji Cao^{a,b}, Haiwei Li^d,

Wingkei Ho,^e and Shun Cheng Lee^d

^aKey Laboratory of Aerosol Chemistry and Physics, State Key Lab of Loess and Quaternary Geology (SKLLQG), Institute of Earth Environment, Chinese Academy of Sciences, Xi'an 710061, China

^bCAS Center for Excellence in Quaternary Science and Global Change, Institute of Earth Environment, Chinese Academy of Sciences, Xi'an 710061, China

^cSchool of Human Settlements and Civil Engineering, Xi'an Jiaotong University, Xi'an 710049, China

^dDepartment of Civil and Environmental Engineering, The Hong Kong Polytechnic University, Hung Hom, Hong Kong, China

^eDepartment of Science and Environmental Studies, The Hong Kong Institute of Education, Hong Kong, China

*Corresponding author: Prof. Yu Huang E-mail address: huangyu@ieecas.cn Tel: +86-02962336261 Supporting Information consists of 13 pages containing 5 method descriptions, 2 tables and 13 figures.

CONTENTS

Method S1. Synthesis of Bi ₂ Sn ₂ O ₇ hollow nanocubes
Method S2. Photoelectrochemical analysis
Method S3. Temperature programmed desorption (TPD) analysis
Method S4. Photocatalytic activity analysis
Method S5. Density Functional Theory (DFT) Calculations
Table S1. Oxygen vacancy formation energies (eV) on the surfaces of $Bi_2Sn_2O_7$.
S7
Table S2. Key structure parameters and adsorption energies of the stable configurations for
the adsorbed species NO on different defect surfaces
Figure S1. Schematic crystal structures of Bi ₂ Sn ₂ O ₇ . Color codes: Bi: purple, Sn: teal, O: red.
Shading regions: pink, tetrahedron; gray, octahedron
Figure S2. EPR spectra of pristine Bi ₂ Sn ₂ O ₇ and Bi ₂ Sn ₂ O _{7-x} samples
Figure S3. (a) TEM and (b) HR-TEM images of Bi ₂ Sn ₂ O ₇
Figure S4. <i>In situ</i> Raman spectrum of pristine Bi ₂ Sn ₂ O ₇ sample in the range from 50 to 400
°C, the inset shows the ball-and-stick model of $Bi_2Sn_2O_7$ coordination and the formation of
oxygen vacancies in different spatial location
Figure S5. Raman spectrum of pristine $Bi_2Sn_2O_7$, V_{O1} - $Bi_2Sn_2O_{7-x}$ and V_{O2} - $Bi_2Sn_2O_{7-x}$



Method S1. Synthesis of Bi₂Sn₂O₇ hollow nanocubes.

BiC₆H₅O₇ (3 mmol) was first added to 35 mL of NaOH solution (1.0 mol·L⁻¹) and then treated by ultrasonic wave for 30 minutes. K₂SnO₃·3H₂O (3 mmol) was dissolved in a Teflon liner with 100 mL capacity containing 35 mL NaOH solution (1.0 mol·L⁻¹) and stirred for a short time. The mixed precipitates were formed by adding BiC₆H₅O₇ suspension to the Sn precursor solution dropwise. The Teflon liner was sealed in the stainless steel autoclave and kept at 180 °C for 24 h. The resulting yellowish powder was collected by washing several times with deionized water and drying at 80 °C.

Method S2. Photoelectrochemical analysis.

The photoelectrochemical properties of pristine $Bi_2Sn_2O_7$ and oxygen-vacancy $Bi_2Sn_2O_{7-x}$ hollow nanocubes were evaluated using a electrochemical workstation (Parstat4000, USA) in a conventional three-electrode cell with a platinum plate and an Ag/AgCl electrode as the counter and reference electrodes, respectively. The photocurrent-time curves were recorded at 0.2 V vs. Ag/AgCl in 0.5 mol·L⁻¹ Na₂SO₃ at ambient temperature under irradiation with a 100 W LED lamp ($\lambda = 420$ nm). Electrochemical impedance spectroscopy (EIS) was conducted under open-circuit voltage in 1 mmol·L⁻¹ K₃Fe(CN)₆ and K₄Fe(CN)₆ solution.

Method S3. Temperature programmed desorption (TPD) analysis.

The TPD experiments were performed on a chemisorption analyzer (BJbuilder, PCA 1200, China) equipped with a thermal conductivity detector (TCD). O_2 -TPD and NO-TPD was performed with 0.5 g and 0.2 g samples using He gas as the carrier gas. The pretreatment of raw sample is firstly applied in pure He with a flow rate of 40 mL·min⁻¹ at 120 °C for 180 min. After the pretreatment sample cooled down to room temperature, O_2 -TPD measurement

was performed up to 800 °C at a heating rate of 7 °C·min⁻¹ in He atmosphere with a flow rate of 25 mL·min⁻¹. The NO–TPD experiments were dosed with 50 ppm NO for 30 min to reach the absorption equilibrium after pretreated with pure He. Then the catalysts were purged with pure He gas with a flow rate of 25 mL·min⁻¹ for 90 min to remove gas-phase NO completely. Finally, NO–TPD was performed up to 800 °C at a heating rate of 7 °C·min⁻¹ in He atmosphere with a flow rate of 25 mL·min⁻¹.

Method S4. Photocatalytic activity analysis.

The photocatalytic activity of as-prepared catalysts were evaluated in a continuous-flow chamber with a 4.5 L capacity (30 cm × 15 cm × 10 cm), which was similar to that in the ISO 22197-1 standard. The removal efficiency of NO was evaluated by 0.2 g of samples pread on a quartz dish placed at the center of the reactor. The initial NO concentrations was 400 ppb for visible light radiation, supplied by a 300 W Xenon lamp through a 420 nm cutoff filter (Perfect Light MICROSOLAR 300, China). After the adsorption-desorption equilibrium by injecting the 400 ppb NO at a volume rate of 3 L·min⁻¹ for at least 30 min, the visible light was turned on and the concentration of NO and NO₂ was continuously measured by a chemiluminescence NOx analyzer (Ecotech 9841, Australia). The removal efficiency of NO at any given time was denoted as C/C_o , where C_o is the initial concentration and of NO, ppb. NO₂ concentration was simultaneously recorded during photocatalytic reaction.

Method S5. Density Functional Theory (DFT) Calculations.

All DFT calculations are performed using the Cambridge Serial Total Energy Package (CASTEP), in which the electron-ion interactions are expressed by ultrasoft pseudo potentials, and the generalized gradient approximation (GGA) proposed by Perdew–Burke–Ernzerhof

(PBE) is used to describe the exchange-correlation energies and potential. The cutoff energy is set as 400 eV. The structure relaxation was performed until the convergence criteria of energy and force reached 2×10^{-5} eV and 0.05 eV/Å, respectively. The Brillouin zone is sampled by a $3\times3\times3$ k-points grid generated via the Monkhorst-Pack procedure. We first optimized the Bi₂Sn₂O₇ unit cell, and calculate the band gap, the results show that the lattice parameter is a = 10.78 Å, which is close to the experimental results (10.87 Å). Meanwhile, the calculated band gap is estimated 2.73 eV. The comparison between the perfect and O vacancy Bi₂Sn₂O₇ were then calculated from the resulting calculation values.

Oxygen vacancy	E _{ads} (eV)
V ₀₁ (Sn-adjacent)	3.15
V _{O2} (Bi-adjacent)	3.67

Table S1. Oxygen vacancy formation energies (eV) on the surfaces of $Bi_2Sn_2O_7$.

Table S2. Key structure parameters and adsorption energies of the stable configurations for

Surface	E _{ads} (eV)	Adsorption	D_{NO-X} (Å)	Bonding details	
		configuration	_	bo	length
				nd	(Å)
$\mathrm{Bi}_2\mathrm{Sn}_2\mathrm{O}_7$	-2.67	top: via N	1.37	N-O	1.23
V ₀₁ -Bi ₂ Sn ₂ O _{7-x} (Sn-adjacent)	-2.84	top: via N	1.32	N-O	1.25
V _{O2} -Bi ₂ Sn ₂ O _{7-x} (Bi-adjacent)	-1.67	hollow: via N	1.89/2.71/2.92	2 N-O	1.25

the adsorbed species NO on different defect surfaces.



Figure S1. Schematic crystal structures of $Bi_2Sn_2O_7$. Color codes: Bi: purple, Sn: teal, O: red.

Shading regions: pink, tetrahedron; gray, octahedron.



Figure S2. EPR spectra of pristine Bi₂Sn₂O₇ and Bi₂Sn₂O_{7-x} samples.



Figure S3. (a) TEM and (b) HR-TEM images of Bi₂Sn₂O₇.



Figure S4. *In situ* Raman spectrum of pristine Bi₂Sn₂O₇ sample in the range from 50 to 400 °C, the inset shows the ball-and-stick model of Bi₂Sn₂O₇ coordination and the formation of oxygen vacancies in different spatial location (inset represents the peak intensity of stretching modes from the Bi-O bonds in Bi₂Sn₂O₇).



Figure S5. Raman spectrum of pristine Bi₂Sn₂O₇, V_{O1}-Bi₂Sn₂O_{7-x} and V_{O2}-Bi₂Sn₂O_{7-x}

samples.



Figure S6. Generation of $\bullet O_2^-$ (a) and $\bullet OH$ (b) over V_{O2} -Bi₂Sn₂O_{7-x}.



Figure S7. Active species trapping for NO removal over (a) $Bi_2Sn_2O_7$, (b) V_{O1} - $Bi_2Sn_2O_{7-x}$ (c)

 $V_{O2}\text{-}Bi_2Sn_2O_{7-x} \text{ with different scavengers (KI \rightarrow h^+; IPA \rightarrow \bullet OH; K_2Cr_2O_7 \rightarrow e^-; PBQ \rightarrow \bullet O_2^-).}$



Figure S8. The band structure for Bi₂Sn₂O₇, V_{O1}-Bi₂Sn₂O_{7-x}(Sn-adjacent) and V_{O2}-Bi₂Sn₂O₇.

_x(Bi-adjacent), respectively.



Figure S9. Electron density difference of $Bi_2Sn_2O_7$, V_{O1} - $Bi_2Sn_2O_{7-x}$ (Sn-adjacent) and V_{O2} -

 $Bi_2Sn_2O_{7-x}(Bi-adjacent)$ samples.



Figure S10. UV-vis DRS spectra of Bi₂Sn₂O₇, V_{O1}-Bi₂Sn₂O_{7-x} and V_{O2}-Bi₂Sn₂O_{7-x}.



Figure S11. The absorption spectra of $Bi_2Sn_2O_7$, V_{O1} - $Bi_2Sn_2O_{7-x}(Sn-adjacent)$ and V_{O2} - $Bi_2Sn_2O_{7-x}(Bi-adjacent)$ as functions of (a) wavelength and (b) energy a using DFT method.



Figure S12. (Ahv)² vs hv of pristine $Bi_2Sn_2O_7$, V_{O1} - $Bi_2Sn_2O_{7-x}$ and V_{O2} - $Bi_2Sn_2O_{7-x}$ samples.



Figure S13. Dielectric Function of Bi2Sn2O7, VO1-Bi2Sn2O7-x(Sn-adjacent) and VO2-

Bi₂Sn₂O_{7-x}(Bi-adjacent): (a) real part (b) imaginary part.